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**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
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Complete if Known

Application Number 09/945500

Filing Date August 30, 2001

First Named Inventor Forbes, Leonard

Group Art Unit Unknown

Examiner Name Unknown

Sheet 1 of 2

Attorney Docket No: 01303.029US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
LP	US-4412902	11/01/1983	Michikami, Osamu, et al	204	192	06/18/1982
	US-4780424	10/25/1988	Holler, Mark A	437	29	09/28/1987
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	US-5852306	12/22/1998	Forbes, Leonard	267	315	01/29/1997
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Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T*
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Examiner Initials *	Class No *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
LP		ARYA, S., "Conduction Properties of Thin Al ₂ O ₃ Films", <u>Thin Solid Films</u> , 91, (1982), pp. 363-374	
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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

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Application Number	09/945500
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 2 of 2

Attorney Docket No: 01303.029US1

OTHER DOCUMENTS - NON PATENT LITERATURE DOCUMENTS

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Substitute Disclosure Statement Form (PTO-1449)
 * EXAMINER: Initial if entry has been considered, whether or not citation is in conformity with MPEP 608. Do not fill through (circle) if not to be considered. Include copy of this form with next communication to applicant. 1 Applicant unique citation (publication number) 2 Applicant to place a check mark here if English language Translation is attached

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Application Number	09/945500
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Pham, Ly

Sheet 1 of 3

Attorney Docket No: 1303.029US1

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	US-2002/0106536	08/08/2002	Lee, Jongho, et al.	428	702	02/02/2001
	US-2002/0137250	09/26/2002	Nguyen, B., et al.	438	53	03/15/2002
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Application Number 09/945500
 Filing Date August 30, 2001
 First Named Inventor Forbes, Leonard
 Group Art Unit 2818
 Examiner Name Pham, Ly

Sheet 2 of 3

Attorney Docket No: 1303.029US1

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OTHER DOCUMENTS - NON PATENT LITERATURE DOCUMENTS

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Application Number 09/945500
 Filing Date August 30, 2001
 First Named Inventor Forbes, Leonard
 Group Art Unit 2818
 Examiner Name Pham, Ly

Sheet 3 of 3

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OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS

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LP		KUKLI, K., "Development of Dielectric Properties of Niobium Oxide, Tantalum Oxide, and Aluminum Oxide Based Nanolayered Materials", <u>Journal of the Electrochemical Society</u> , 148(2), (2001), pp. F35-F41	
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	US-2003/0043622	03/06/2003	Forbes, Leonard	365	185.05	08/30/2001
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EXAMINER

DATE CONSIDERED

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Substitute Disclosure Statement Form (PTO-1440)
 * EXAMINER: Initials of reference considered, whether or not citation is in conformity with MPEP 2112. Disclose line through citation if not in conformity and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) is a reference to prior art. Check mark here if English language Translation is attached.

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 First Named Inventor Forbes, Leonard
 Group Art Unit 2818
 Examiner Name Pham, Ly

Sheet 2 of 2

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LP	US-6,101,131	08/08/2000	Chang, Ming-Bing	365	185.33	04/22/1999
	US-6,127,227	10/03/2000	Lin, Chrong J., et al.	438	261	01/26/1999
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FOREIGN PATENT DOCUMENTS

Examiner Initials	Foreign Document No.	Publication Date	Name of Patent or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
LP		BHATTACHARYYA, A., "Physical & Electrical Characteristics of LPCVD Silicon Rich Nitride", ECS Technical Digest, J. Electrochem. Soc., 131(11), 691 RDP, New Orleans, (1984), 489C	
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10/03/2004

Substitute Disclosure Statement Form (PTO-1448)
 * EXAMINER: Initial if document is considered, whether or not claim is in conformity with prior art. Draw line through citation if not in conformity and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is attached.